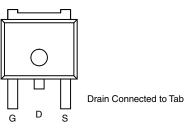


30 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY

V _{DS} (V)	40
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 V$	0.0035
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 V$	0.0042
I _D (A)	50
Configuration	Single





Top View

FEATURES

- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- AEC-Q101 Qualified
- 100 % R_g and UIS Tested

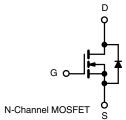


COMPLIANT

HALOGEN

FREE

• Material categorization: For definitions of compliance please see www.freescale.net.cn



ORDERING INFORMATION				
Package	TO-252			
Lead (Pb)-free and Halogen-free	SQD50N04-3m5L-GE3			

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		V _{DS}	40			
Gate-Source Voltage		V _{GS}	± 20	V		
Continuous Drain Current ^a	T _C = 25 °C	I	50			
	T _C = 125 °C	I _D	50			
Continuous Source Current (Diode Conduction) ^a		I _S	50	А		
Pulsed Drain Current ^b		I _{DM}	200			
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	55			
Single Pulse Avalanche Energy		E _{AS}	151	mJ		
Maximum Power Dissipation ^b	T _C = 25 °C	PD	136	W		
	T _C = 125 °C	۲D	45	vv		
Operating Junction and Storage Temperature Rang	je	T _J , T _{stg}	- 55 to + 175	°C		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	50	°C/W	
Junction-to-Case (Drain)		R _{thJC}	1.1	C/W	

Notes

a. Package limited.

b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

c. When mounted on 1" square PCB (FR-4 material).



SQD50N04-3m5L Automotive N-Channel

30 V (D-S) 175 °C MOSFET

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static					•			
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 V, I_D = 250 \mu A$		40	-	-	v	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	1.5	-	2.5	v	
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = 40 V	-	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 40 V, T _J = 125 °C	-	-	50	μA	
		$V_{GS} = 0 V$	V _{DS} = 40 V, T _J = 175 °C	-	-	150		
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	50	-	-	Α	
		V _{GS} = 10 V	I _D = 20 A	-	0.0029	0.0035	Ω	
Ducia Course On Otata Decistance?		V _{GS} = 10 V	I _D = 20 A, T _J = 125 °C	-	-	0.0056		
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 10 V$	I _D = 20 A, T _J = 175 °C	-	-	0.0068		
		V _{GS} = 4.5 V	I _D = 20 A	-	0.0034	0.0042		
Forward Transconductanceb	9 _{fs}	V _{DS}	= 15 V, I _D = 15 A	-	105	-	S	
Dynamic ^b	•						•	
Input Capacitance	C _{iss}		V _{GS} = 0 V V _{DS} = 25 V, f = 1 MHz	-	4880	5860	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$		-	560	670		
Reverse Transfer Capacitance	C _{rss}	1		-	250	300		
Total Gate Charge ^c	Qg			-	85	130		
Gate-Source Charge ^c	Q _{gs}	$V_{GS} = 10 V$	$V_{DS} = 20 \text{ V}, \text{ I}_{D} = 50 \text{ A}$	-	14	-	nC	
Gate-Drain Charge ^c	Q _{gd}	1		-	14	-		
Gate Resistance	Rg	f = 1 MHz		1	2	3	Ω	
Turn-On Delay Time ^c	t _{d(on)}				9	11		
Rise Time ^c	t _r	$\label{eq:VDD} \begin{array}{l} V_{DD} = 20 \; V, \; R_{L} = 0.4 \; \Omega \\ I_{D} \cong 50 \; A, \; V_{GEN} = 10 \; V, \; R_{g} = 1 \; \Omega \end{array}$		-	11	14	ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	39	47		
Fall Time ^c	t _f			-	11	14		
Source-Drain Diode Ratings and Char	acteristics ^b	•						
Pulsed Current ^a	I _{SM}			-	-	200	Α	
Forward Voltage	V _{SD}	I _F = 30 A, V _{GS} = 0 V		_	0.9	1.5	V	

Notes

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

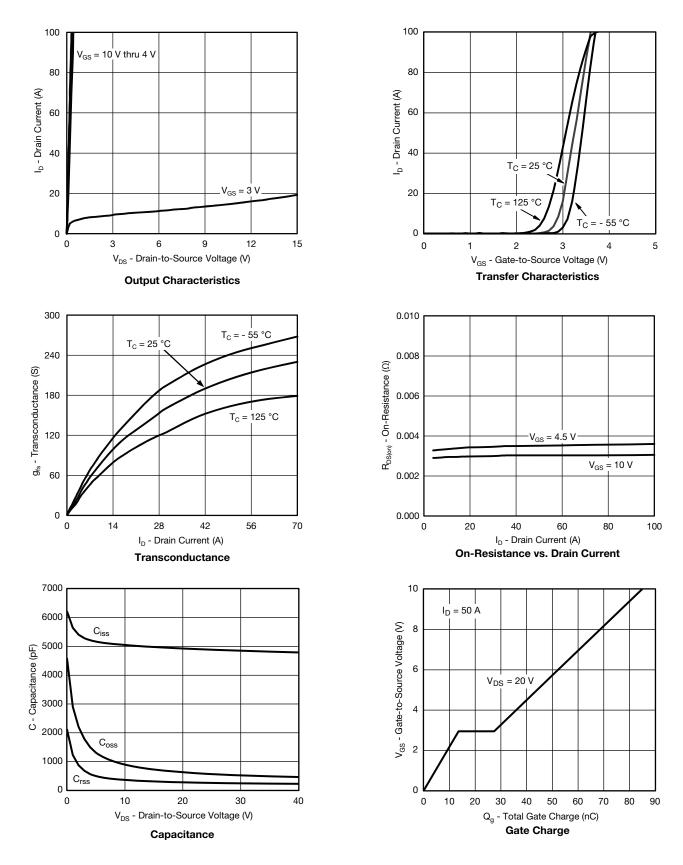
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



SQD50N04-3m5L Automotive N-Channel 30 V (D-S) 175 °C MOSFET

TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

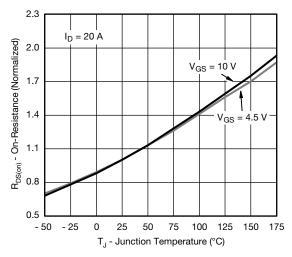




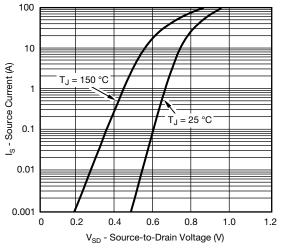
SQD50N04-3m5L Automotive N-Channel

30 V (D-S) 175 °C MOSFET

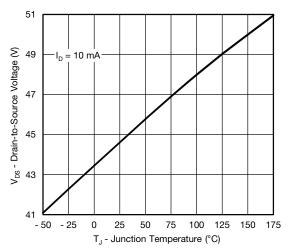
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



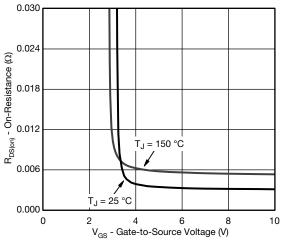
On-Resistance vs. Junction Temperature



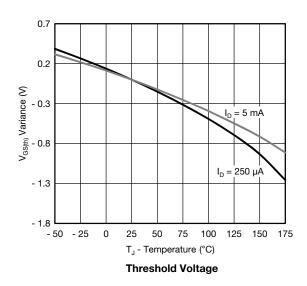
Source Drain Diode Forward Voltage



Drain Source Breakdown vs. Junction Temperature



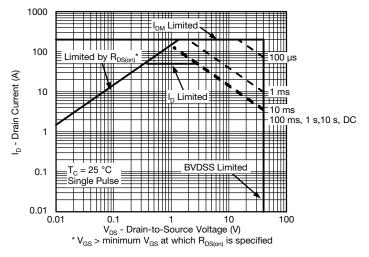
On-Resistance vs. Gate-to-Source Voltage



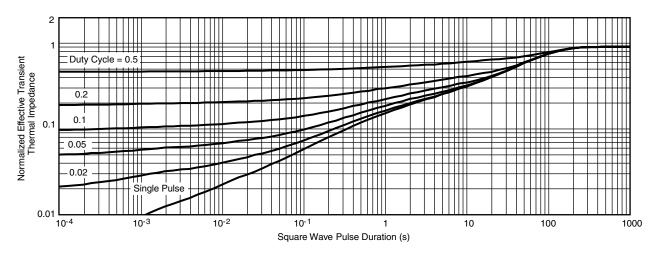


SQD50N04-3m5L Automotive N-Channel 30 V (D-S) 175 °C MOSFET

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Safe Operating Area



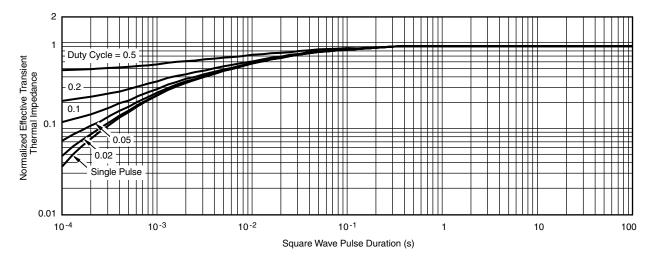
Normalized Thermal Transient Impedance, Junction-to-Ambient



SQD50N04-3m5L Automotive N-Channel

30 V (D-S) 175 °C MOSFET

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

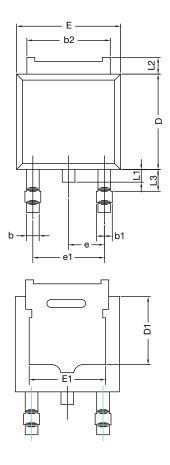
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

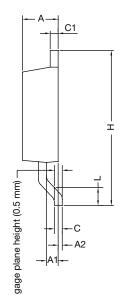
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.



SQD50N04-3m5L Automotive N-Channel 30 V (D-S) 175 °C MOSFET

TO-252AA CASE OUTLINE





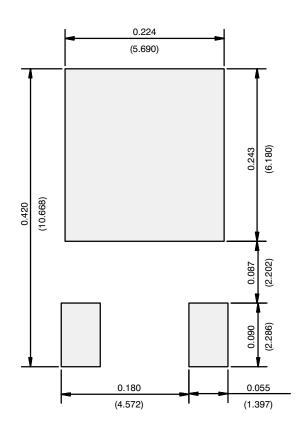
	MILLIN	IETERS	INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
А	2.21	2.38	0.087	0.094	
A1	0.89	1.14	0.035	0.045	
A2	0.030	0.127	0.001	0.005	
b	0.71	0.88	0.028	0.035	
b1	0.76	1.14	0.030	0.045	
b2	5.23	5.44	0.206	0.214	
С	0.46	0.58	0.018	0.023	
C1	0.46	0.58	0.018	0.023	
D	5.97	6.22	0.235	0.245	
D1	4.10	4.45	0.161	0.175	
E	6.48	6.73	0.255	0.265	
E1	4.49	5.50	0.177	0.217	
е	2.28	BSC	0.090 BSC		
e1	4.57 BSC		0.180 BSC		
Н	9.65	10.41	0.380	0.410	
L	1.40	1.78	0.055	0.070	
L1	0.64	1.02	0.025	0.040	
L2	0.89	1.27	0.035	0.050	
L3	1.15	1.52	0.040	0.060	
ECN: T11-0110-Rev. L, 18-Apr-11 DWG: 5347					

Note

• Dimension L3 is for reference only.



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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